

ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

Title of Invention	METHOD FOR GROWING A GATE OXIDE LAYER ON A SILICON SURFACE WITH PRELIMINARY N2O ANNEAL
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Application Number :

Confirmation Number:

First Named Applicant: Shian-Jyh Lin

Attorney Docket Number: NTCP0014USA

Art Unit:

Examiner:

Search string: (6184110 or 6204205 or 6498365).pn

US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
	1	6184110	2001-02-06	Ono, et al.			
	2	6204205	2001-03-20	Yu, et al.			
	3	6498365	2002-12-24	Wakamiya			

Signature

Examiner Name	Date